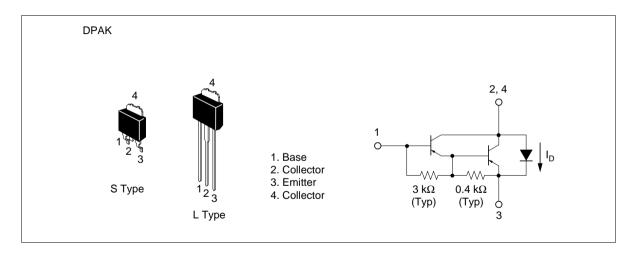
# Silicon PNP Triple Diffused

# **HITACHI**

### **Application**

Medium speed power amplifier

#### Outline





## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

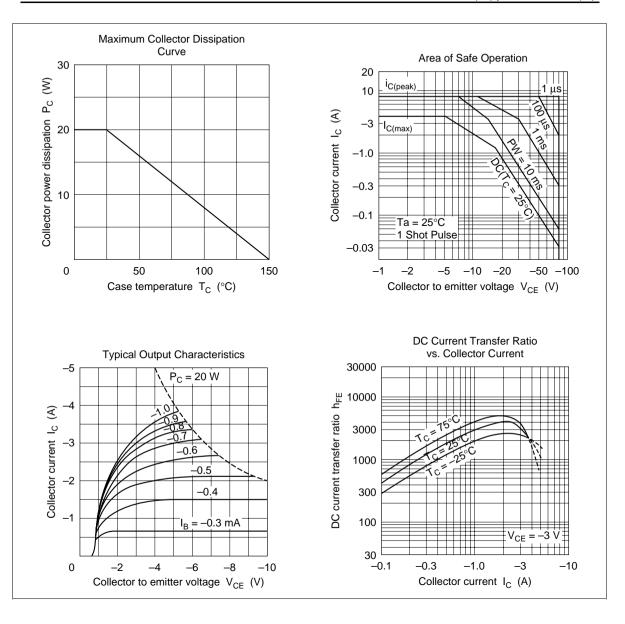
Item	Symbol	Rating	Unit	
Collector to base voltage	V <sub>CBO</sub>	-100	V	
Collector to emitter voltage	V <sub>CEO</sub>	-80	V	
Emitter to base voltage	$V_{EBO}$	<b>-</b> 7	V	
Collector current	I <sub>c</sub>	-4	A	
C to E diode forward current	I <sub>D</sub> *1	4	A	
Collector peak current	I <sub>C(peak)</sub>	-8	A	
Collector power dissipation	P <sub>c</sub> *1	20	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

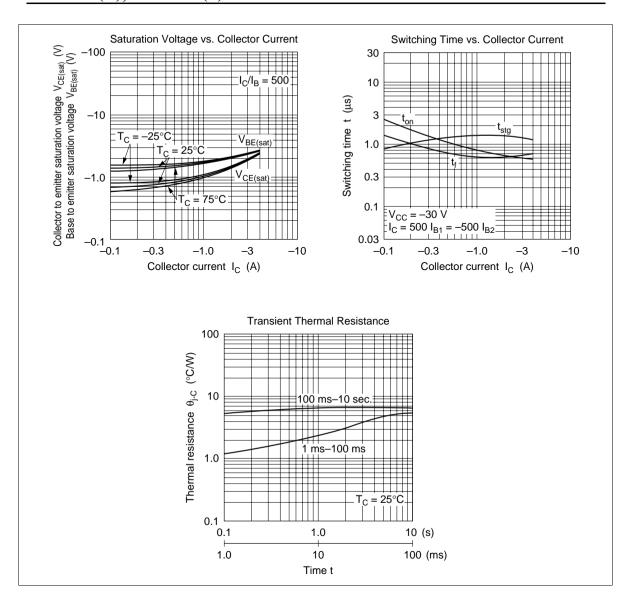
Note: 1. Value at  $T_c = 25^{\circ}C$ 

## **Electrical Characteristics** (Ta = 25°C)

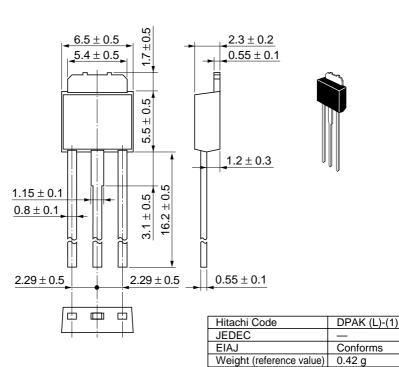
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-80	_	_	V	$I_{\rm C}$ = -25 mA, $R_{\rm BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>-7</b>	_	_	V	$I_{E} = -50 \text{ mA}, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-100	μΑ	$V_{CB} = -80 \text{ V}, I_{E} = 0$
	I <sub>CEO</sub>	_	_	-10	μΑ	V <sub>CE</sub> = -60 V, R <sub>BE</sub> = ∞
DC current transfer ratio	h <sub>FE</sub>	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -2 \text{ A}^{*1}$
Collector to emitter saturation	$V_{\text{CE(sat)1}}$	_	_	-1.5	V	$I_{\rm C} = -2 \text{ A}, I_{\rm B} = -4 \text{ mA}^{*1}$
voltage	V <sub>CE(sat)2</sub>	_	_	-3.0	V	$I_{\rm C} = -4 \text{ A}, I_{\rm B} = -40 \text{ mA}^{*1}$
Base to emitter saturation	$V_{BE(sat)1}$	_	_	-2.0	V	$I_{\rm C} = -2 \text{ A}, I_{\rm B} = -4 \text{ mA}^{*1}$
voltage	$V_{BE(sat)2}$	_	_	-3.5	V	$I_{\rm C} = -4 \text{ A}, I_{\rm B} = -40 \text{ mA}^{*1}$
C to E diode forward voltage	V <sub>D</sub>	_	_	3.0	V	I <sub>D</sub> = 4 A* <sup>1</sup>
Turn on time	t <sub>on</sub>	_	0.5	_	μs	$I_{\rm C} = -2 \text{ A}, I_{\rm B1} = -I_{\rm B2} = -4 \text{ mA}$
Storage time	t <sub>stg</sub>	_	1.5	_	μs	
Fall time	t <sub>f</sub>	_	1.0	_	μs	_

Note: 1. Pulse test.





Unit: mm



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